



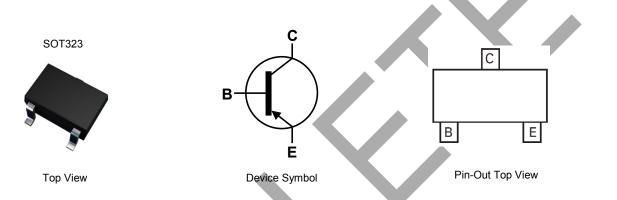
#### 25V PNP SMALL SIGNAL TRANSISTOR IN SOT323

#### **Features**

- $BV_{CEO} > -25V$
- I<sub>C</sub> = -200mA Collector Current
- **Epitaxial Planar Die Construction**
- Ultra-Small Surface Mount Package
- Complementary NPN Type: MMST4124
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT323
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)



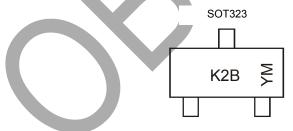
# Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
MMST4126-7-F	Standard	K2B	7	8	3,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**



K2B = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: D = 2016) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Date Code														
Year	201	10	2011		2012	2013	2014	2015	201	6 20	17 2	2018	2019	2020
Code	X		Υ		Z	Α	В	С	D	Е		F	G	Н
Mont	h	Ja	n F	eb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	)	1		2	3	4	5	6	7	8	9	0	N	D



# **Absolute Maximum Ratings** (@ $T_A = +25^{\circ}C$ unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-25	V
Emitter-Base Voltage	V <sub>EBO</sub>	-4	V
Collector Current	I <sub>C</sub>	-200	mA

## Thermal Characteristics (@TA = +25°C unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	$P_d$	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	$T_{j}$ , $T_{STG}$	-55 to +150	°C

## ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is
- measured under still air conditions whilst operating in a steady-state.

  6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## **Thermal Characteristics and Derating Information**

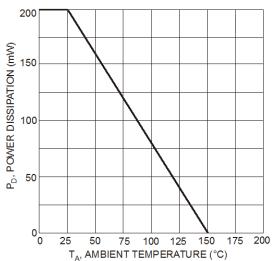


Fig. 1 Max Power Dissipation vs. Ambient Temperature



## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

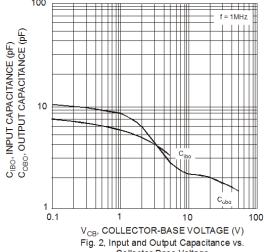
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	,				
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-25	_	V	$I_C = -10\mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-25	_	V	I <sub>C</sub> = -1mA, I <sub>B</sub> = 0
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	V	$I_E = -10\mu A, I_C = 0$
Collector Base Cut-Off Current	I <sub>CBO</sub>	_	-50	nA	$V_{CB} = -20V, I_{E} = 0$
Collector Cut-Off Current	I <sub>EBO</sub>	_	-50	nA	V <sub>EB</sub> = 5V, I <sub>E</sub> = 0
ON CHARACTERISTICS (Note 7)					
DC Current Gain	h	120	360		$I_C = -2.0 \text{mA}, V_{CE} = -1.0 \text{V}$
DC Current Gain	h <sub>FE</sub>	60	_	_	$I_C = -50 \text{mA}, V_{CE} = -1.0 \text{V}$
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	_	-0.40	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	_	-0.95	V	$I_C = -50 \text{mA}, I_B = -5.0 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	$C_{obo}$	_	4.5	pF	$V_{CB} = -5.0V$ , $f = 1.0MHz$ , $I_E = 0$
Input Capacitance	C <sub>ibo</sub>		10	pF	$V_{EB} = -0.5V$ , $f = 1.0MHz$ , $I_C = 0$
Small Signal Current Gain	h <sub>fe</sub>	120	480	_	$V_{CE} = 1.0V, I_{C} = -2.0mA, f = 1.0kHz$
Current Gain-Bandwidth Product	f <sub>T</sub>	250	_	MHz	V <sub>CE</sub> = -20V, I <sub>C</sub> = -10mA, f = 100MHz
Noise Figure	NF		4.0	dB	$V_{CE}$ = -5.0V, $I_{C}$ = -100 $\mu$ A, $R_{S}$ = 1.0k $\Omega$ , f = 1.0kHz

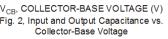
Note: 7. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .





## Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





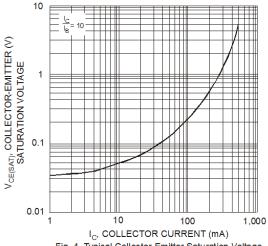


Fig. 4, Typical Collector-Emitter Saturation Voltage vs. Collector Current

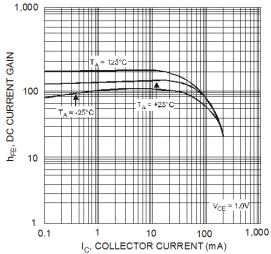


Fig. 3, Typical DC Current Gain vs.
Collector Current

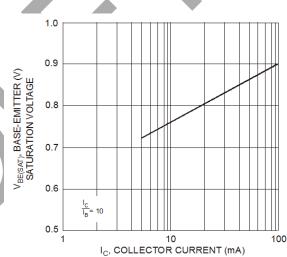
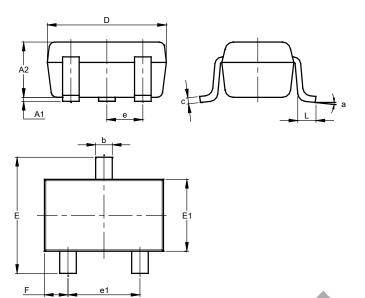


Fig. 5, Typical Base-Emitter Saturation Voltage vs. Collector Current



# **Package Outline Dimensions**

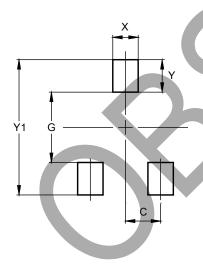
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT323							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.25	0.40	0.30				
С	0.10	0.18	0.11				
D	1.80	2.20	2.15				
E	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C	).650 B	SC				
e1	1.20	1.40	1.30				
F	0.375	0.475	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All Dimensions in mm							

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.470
Y	0.600
Y1	2.500



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